

## READOUT AND REWRITE-IN METHOD FOR DYNAMIC MOS SEMICONDUCTOR MEMORY

Veröffentlichungsnummer JP57018080

Veröffentlichungsdatum: 1982-01-29

Erfinder: TANIGUCHI MAKOTO

Anmelder: MITSUBISHI ELECTRIC CORP

Klassifikation:

- Internationale: G11C11/407; G11C11/408; G11C11/407;  
G11C11/408; (IPC1-7): G11C11/34

- Europäische: G11C11/408C

Anmeldenummer: JP19800093451 19800707

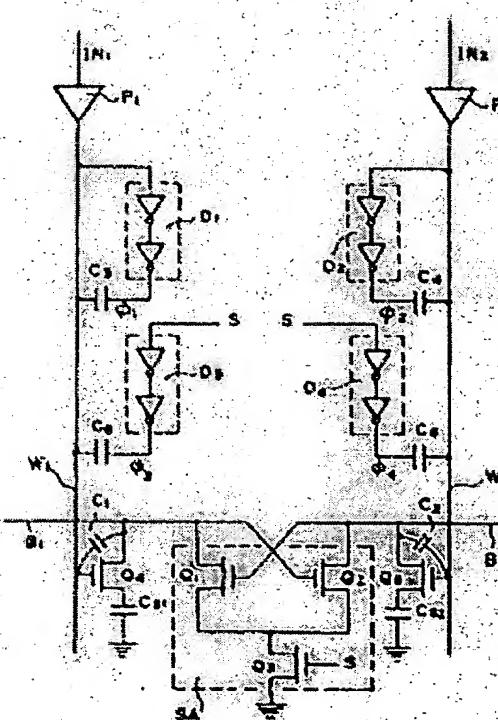
Prioritätsnummer(n): JP19800093451 19800707

[Datenfehler hier melden](#)

### Zusammenfassung von JP57018080

PURPOSE: To assure the readout and rewrite-in voltage to a memory cell, by boosting the word line drive pulse more than the power supply voltage before the operation of sense amplifier circuit and boosting it once more after the operation of the sense amplifier circuit.

CONSTITUTION: First, boosting capacitors C3, C4 are charged with boosting pulses phi1, phi2 outputted from delay circuits D1, D2 after a given time through the input of word line drive pulse WP, to boost the word lines W1, W2. Futher, a sense amplifier, drive signal S is inputted to delay circuits D3, D4 and word line boosting pulses phi3, phi4 is outputted after a given time. The boosting capacitors C3, C6 are charged with the word line boosting pulses phi3, phi4 and the word lines W1, W2 are boosted again. Thus, the potential of the word lines W1, W2 can be assured sufficiently highly.



Daten sind von der [esp@cenet](mailto:esp@cenet) Datenbank verfügbar - Worldwide